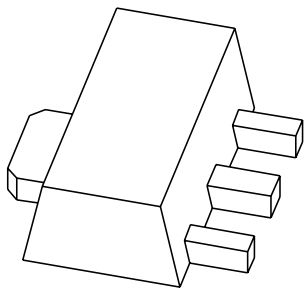


DATA SHEET



BFQ591 NPN 7 GHz wideband transistor

Product specification
Supersedes data of 2002 Jan 07

2002 Feb 04

NPN 7 GHz wideband transistor

BFQ591

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscribers equipment.

DESCRIPTION

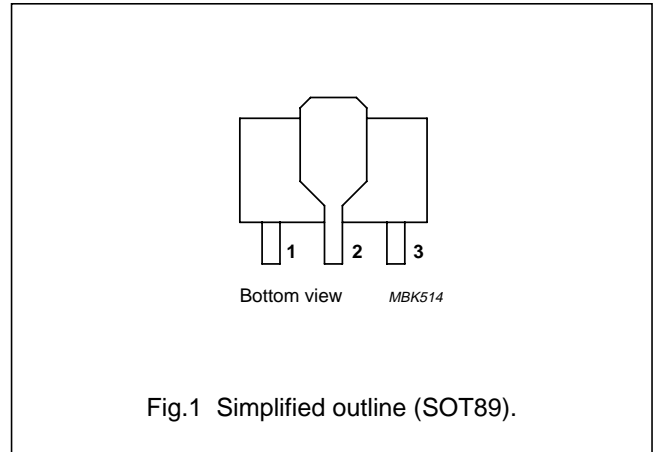
NPN wideband transistor in a SOT89 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BFQ591	BCp

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	$T_s \leq 90\text{ }^\circ\text{C}$; note 1	–	–	2.25	W
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 12\text{ V}$; $f = 1\text{ MHz}$	–	0.8	–	pF
f_T	transition frequency	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 1\text{ GHz}$	–	7	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	11	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	10	–	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	200	mA
P_{tot}	total power dissipation	$T_s \leq 90\text{ °C}$; note 1	–	2.25	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C

Note

- T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s \leq 90\text{ °C}$; note 1	38	K/W

Note

- T_s is the temperature at the soldering point of the collector pin.

NPN 7 GHz wideband transistor

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CHARACTERISTICST_j = 25 °C; unless otherwise specified.

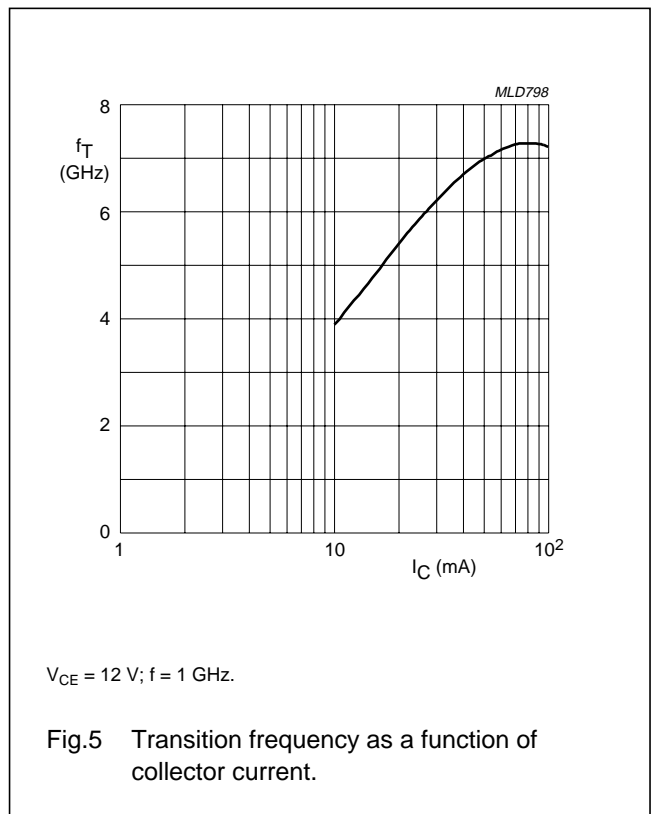
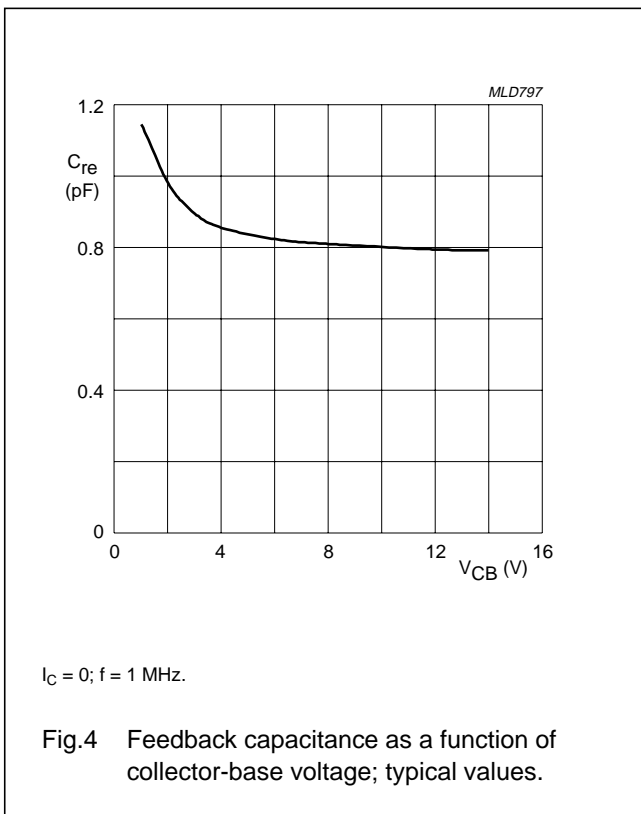
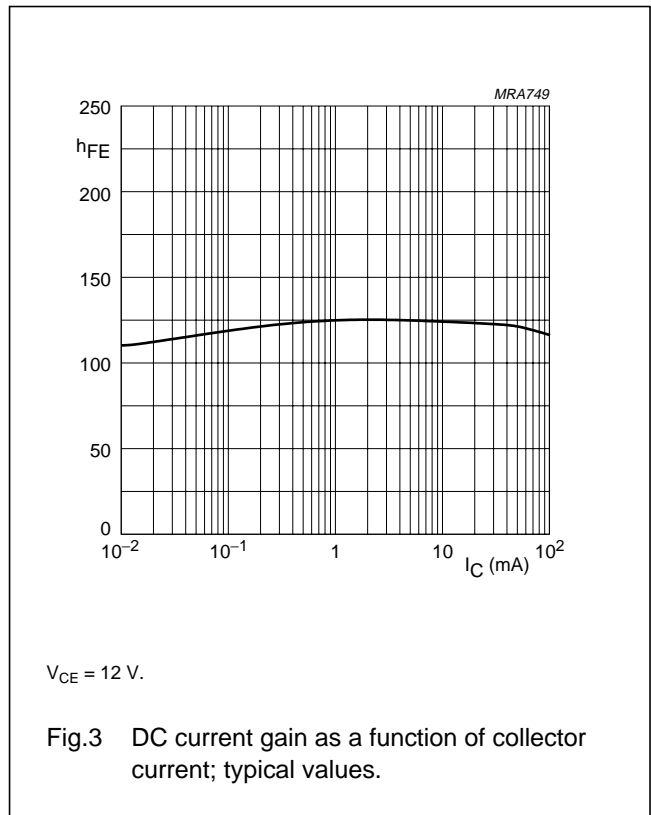
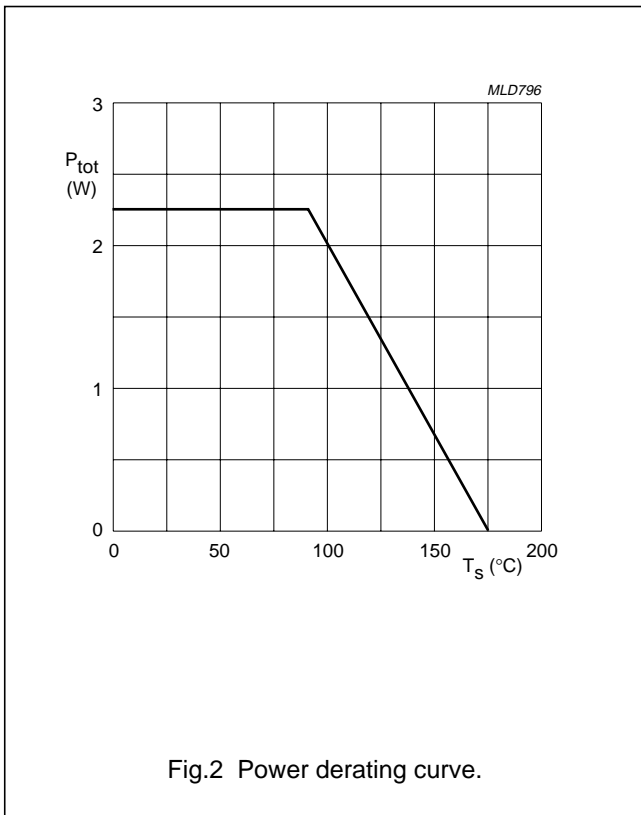
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 0.1 mA; I _E = 0	–	–	20	V
V _{(BR)CES}	collector-emitter breakdown voltage	I _C = 0.1 mA; I _B = 0	–	–	15	V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 0.1 mA; I _C = 0	–	–	3	V
I _{CBO}	collector-base leakage current	I _E = 0; V _{CB} = 10	–	–	100	nA
h _{FE}	DC current gain	I _C = 70 mA; V _{CE} = 8 V	60	90	250	
C _{re}	feedback capacitance	I _C = 0; V _{CB} = 12 V; f = 1 MHz	–	0.8	–	pF
f _T	transition frequency	I _C = 70 mA; V _{CE} = 12 V; f = 1 GHz	–	7	–	GHz
G _{UM}	maximum unilateral power gain; note 1	I _C = 70 mA; V _{CE} = 12 V; T _{amb} = 25 °C f = 900 MHz f = 2 GHz	–	11 5.5	–	dB dB
S ₂₁ ²	insertion power gain	I _C = 70 mA; V _{CE} = 12 V; f = 1 GHz; T _{amb} = 25 °C	–	10	–	dB
V _o	output voltage	note 2	–	700	–	mV

Notes

- G_{UM} is the maximum unilateral power gain, assuming s₁₂ is zero and $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB.
- d_{im} = 60 dB (DIN45004B); V_p = V_o; V_q = V_o – 6 dB; f_p = 795.25 MHz; f_q = 803.25 MHz; f_r = 803.25 MHz; measured at f_(p+q+r) = 793.25 MHz.

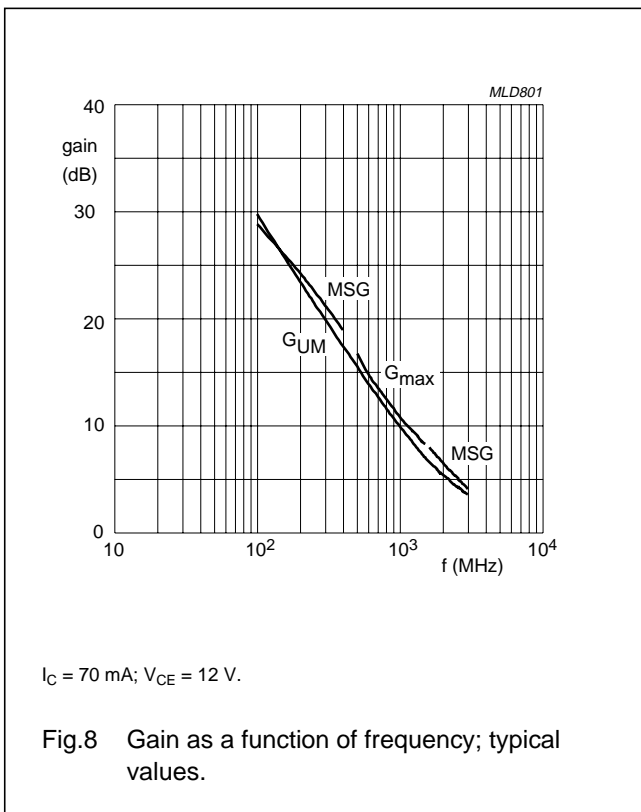
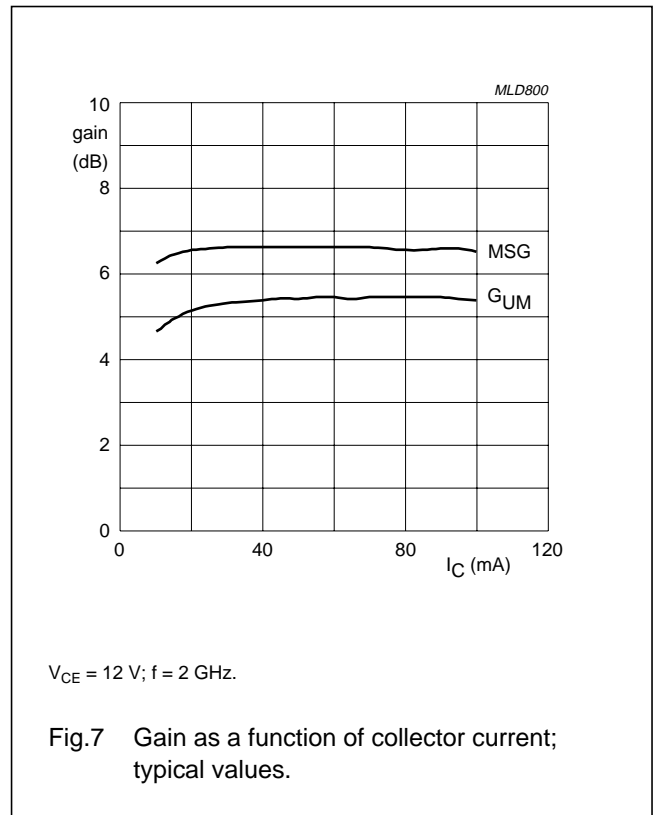
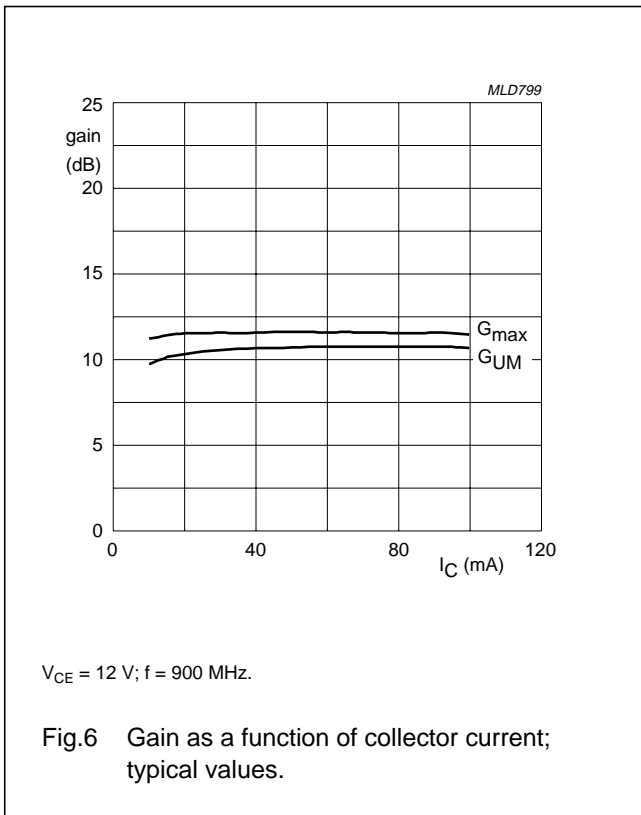
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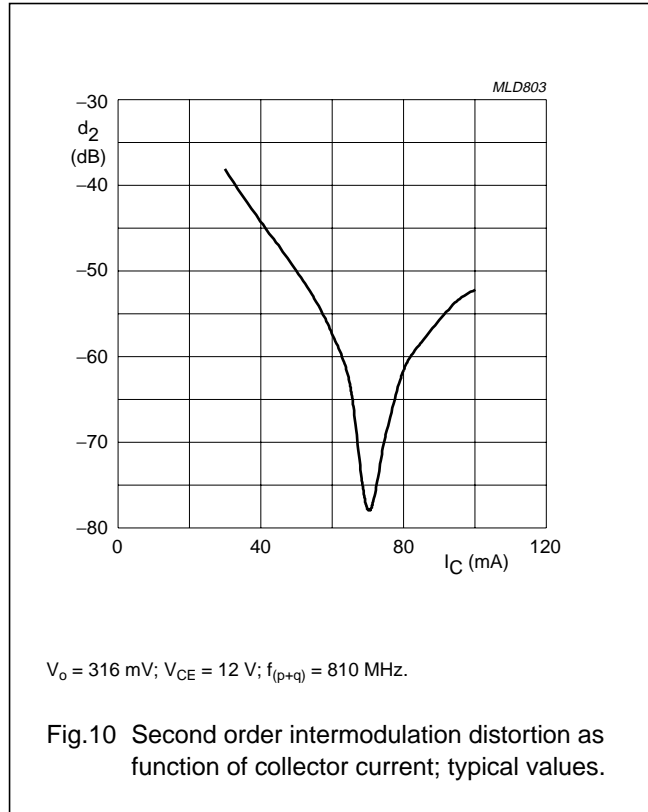
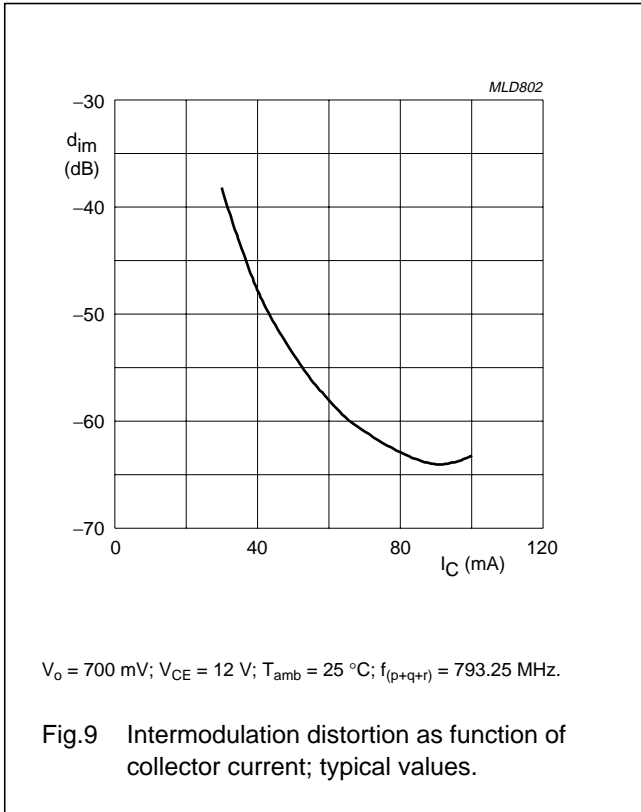
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NPN 7 GHz wideband transistor

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NPN 7 GHz wideband transistor

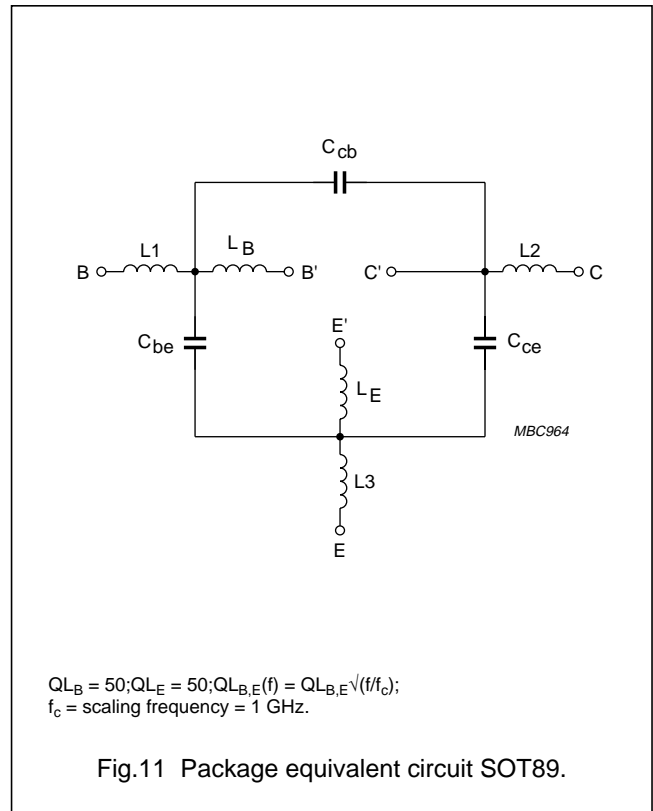
BFQ591

SPICE parameters for the BFQ591 die.

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	.988	–
4	VAF	75.85	V
5	IKF	9.656	mA
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	997.2	–
14	RB	5.00	Ω
15	IRB	1.000	μA
16	RBM	5.00	Ω
17	RE	1.275	Ω
18	RC	920.6	Ω
19 ⁽¹⁾	XTB	0.000	–
20 ⁽¹⁾	EG	1.110	eV
21 ⁽¹⁾	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	348.5	–
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	mA
29	PTF	0.000	deg
30	CJC	1.409	fF
31	VJC	219.4	mV
32	MJC	166.5	–
33	XCJ	2.340	–
34	TR	543.7	ps
35 ⁽¹⁾	CJS	0.000	F
36 ⁽¹⁾	VJS	750.0	mV
37 ⁽¹⁾	MJS	0.000	–
38	FC	733.2	–

Note

1. These parameters have not been extracted, the default values are shown.



List of components (see Fig.11)

DESIGNATION	VALUE	UNIT
C _{be}	16	fF
C _{cb}	150	fF
C _{ce}	150	fF
L1	1	nH
L2	0.01	nH
L3	1	nH
L _B	1.2	nH
L _E	1.2	nH

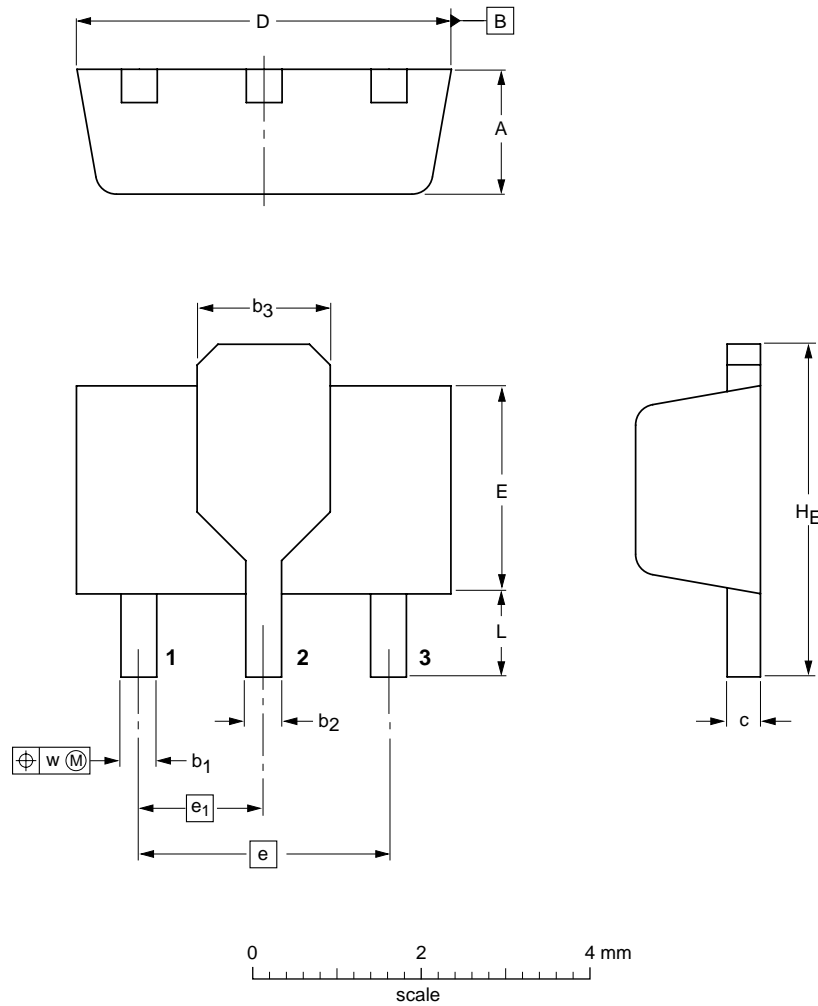
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b ₁	b ₂	b ₃	c	D	E	e	e ₁	H _E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT89		TO-243	SC-62		97-02-28 99-09-13

NPN 7 GHz wideband transistor

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Printed in The Netherlands

613516/03/pp12

Date of release: 2002 Feb 04

Document order number: 9397 750 09271

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